

LETTERS

X-ray photoelectron spectroscopy study of polyimide thin films with Ar cluster ion depth profiling

T. Miyayama, N. Sanada, M. Suzuki, J. S. Hammond, S.-Q. D. Si and A. Takahara
J. Vac. Sci. Technol. A **28**, L1 (2010); <http://dx.doi.org/10.1116/1.3336242>

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Modifying the composition of hydrogen-terminated silicon nanoparticles synthesized in a nonthermal rf plasma

Jason Holm and Jeffrey T. Roberts
J. Vac. Sci. Technol. A **28**, 161 (2010); <http://dx.doi.org/10.1116/1.3276451>

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Photoconduction in silicon rich oxide films obtained by low pressure chemical vapor deposition

J. A. Luna-López, M. Aceves-Mijares, J. Carrillo-López and A. Morales-Sánchez
J. Vac. Sci. Technol. A **28**, 170 (2010); <http://dx.doi.org/10.1116/1.3276781>

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Coexistence of epitaxial Ta(111) and Ta(110) oriented magnetron sputtered thin film on c-cut sapphire

S. Gnanarajan, S. K. H. Lam and A. Bendavid
J. Vac. Sci. Technol. A **28**, 175 (2010); <http://dx.doi.org/10.1116/1.3276801>

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Comparison of compressive and tensile relaxed composition-graded GaAsP and (Al)InGaP substrates

M. J. Mori, S. T. Boles and E. A. Fitzgerald
J. Vac. Sci. Technol. A **28**, 182 (2010); <http://dx.doi.org/10.1116/1.3290762>

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Fast and smooth etching of indium tin oxides in BCl_3/Cl_2 inductively coupled plasmas

H. B. Andagana and X. A. Cao
J. Vac. Sci. Technol. A **28**, 189 (2010); <http://dx.doi.org/10.1116/1.3280919>

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Influence of the magnetron on the growth of aluminum nitride thin films deposited by reactive sputtering

G. F. Iriarte
J. Vac. Sci. Technol. A **28**, 193 (2010); <http://dx.doi.org/10.1116/1.3280174>

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J. Musil, P. Novák, R. Čerstvý and Z. Soukup

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Etching of SiO₂ in C₄F₈/Ar plasmas. I. Numeric kinetics modeling and Monte Carlo simulation in a three-dimensional profile simulator

Wei Guo and Herbert H. Sawin

J. Vac. Sci. Technol. A **28**, 250 (2010); <http://dx.doi.org/10.1116/1.3290760>

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Etching of SiO₂ in C₄F₈/Ar plasmas. II. Simulation of surface roughening and local polymerization

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Sr flux stability against oxidation in oxide-molecular-beam-epitaxy environment: Flux, geometry, and pressure dependence

Y. S. Kim, Namrata Bansal, Carlos Chaparro, Heiko Gross and Seongshik Oh

J. Vac. Sci. Technol. A **28**, 271 (2010); <http://dx.doi.org/10.1116/1.3298880>

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Etching studies of silica glasses in SF₆/Ar inductively coupled plasmas: Implications for microfluidic devices fabrication

L. Lallement, C. Gosse, C. Cardinaud, M.-C. Peignon-Fernandez and A. Rhallabi

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Surface-charging effect of capacitively coupled plasmas driven by combined dc/rf sources

Quan-Zhi Zhang, Wei Jiang, Shu-Xia Zhao and You-Nian Wang

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Amorphization of Si(100) by Ar^+ -ion bombardment studied with spectroscopic and time-resolved second-harmonic generation

P. M. Gevers, J. J. H. Gielis, H. C. W. Beijerinck, M. C. M. van de Sanden and W. M. M. Kessels

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TaN metal gate etch mechanisms in BCl_3 -based plasmas

Denis Shamiryan, Andrey Danila, Mikhail R. Baklanov and Werner Boullart

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Quantum turbulence at room temperature

C. Llaguno and A. Muriel

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Self-bias voltage diagnostics for the amorphous-to-microcrystalline transition in a-Si:H under a hydrogen-plasma treatment

A. Hadjadj, N. Pham, P. Roca i Cabarrocas and O. Jbara

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Combinatorial characterization of transparent conductive properties of Ga-doped ZnO films cosputtered from electron cyclotron resonance and rf magnetron plasma sources

Housei Akazawa

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Plasma kinetics of Ar/O_2 magnetron discharge by two-dimensional multifluid modeling

C. Costin, T. M. Minea, G. Popa and G. Gousset

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Effects of working pressure on physical properties of tungsten-oxide thin films sputtered from oxide target

I. Riech, M. Acosta, J. L. Peña and P. Bartolo-Pérez

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Model for aspect ratio dependent etch modulated processing

Peter J. Gilgunn, J. Fernando Alfaro and Gary K. Fedder

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Characterization of worn Ti-Si cathodes used for reactive cathodic arc evaporation

J. Q. Zhu, A. Eriksson, N. Ghafoor, M. P. Johansson, J. Sjöln, L. Hultman, J. Rosén and M. Odén

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β -Ga₂O₃ growth by plasma-assisted molecular beam epitaxy^{a)}

Min-Ying Tsai, Oliver Bierwagen, Mark E. White and James S. Speck

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Surface loss rates of H and Cl radicals in an inductively coupled plasma etcher derived from time-resolved electron density and optical emission measurements

G. A. Curley, L. Gatilova, S. Guilet, S. Bouchoule, G. S. Gogna, N. Sirse, S. Karkari and J. P. Booth

J. Vac. Sci. Technol. A **28**, 360 (2010); <http://dx.doi.org/10.1116/1.3330766>

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Surface modification of phyllosilicate minerals by fluorination methods

Alain Tressaud, Christine Labrugère, Etienne Durand, Hélène Serier and Larisa P. Demyanova

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